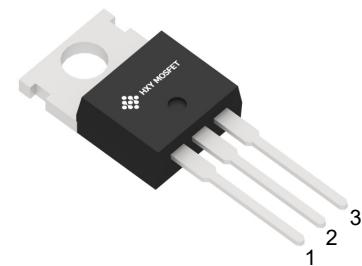




Features

- Wide bandgap SiC MOSFET technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed switching
- Low reverse recovery(Qrr)
- Halogen free, RoHS compliant



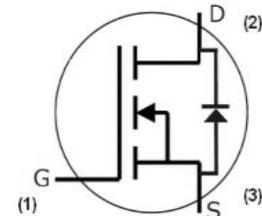
TO-220C

Benefits

- Reduce switching losses
- Increased system Switching Frequency
- Increased power density
- Reduction of heat sink requirements

Applications

- Switch mode power supplies
- Renewable energy
- On Board Charger
- High Voltage DC/DC Converters



Ordering Part Number	Package	Brand
MSJP20N65A-BP	TO-220C	HXY MOSFET

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit	Note
V_{DSmax}	Drain-Source Voltage	$V_{GS} = 0\text{V}$, $I_D = 100\mu\text{A}$	800	V	
V_{GSmax}	Gate-Source voltage	AC ($f > 1\text{ Hz}$)	-10/+25	V	
V_{GSop}	Recommend Gate-Source Voltage	Static	-4/+18 -4/+15	V	
EAS	Single pulse avalanche energy	$V_{DS}=800\text{V}$, $V_{DD}=50\text{V}$, $V_{GS}=10\text{V}$, $L=10\text{mH}$, $T_c=25^\circ\text{C}$	205	mJ	
I_D	Continuous Drain current	$V_{GS} = 18\text{V}$, $T_c = 25^\circ\text{C}$	20	A	Fig. 14
		$V_{GS} = 18\text{V}$, $T_c = 100^\circ\text{C}$	11		
$I_{D,pulse}$	Pulsed Drain Current	Pulse with t_p limited by T_{jmax}	26	A	
P_D	Power Dissipation	$T_c = 25^\circ\text{C}$, $T_j = 175^\circ\text{C}$	83	W	Fig. 16
T_j	Operating junction temperature		-55~175	°C	
T_{stg}	Storage temperature		-55~175	°C	



Thermal Characteristics

Symbol	Parameter	Value			Unit	Note
		Min.	Typ.	Max.		
$R_{th(jc)}$	Thermal resistance from Junction to Case		1.8		K/W	Fig. 15
$R_{th(ja)}$	Thermal resistance from Junction to Ambient		40		K/W	

Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note	
			Min.	Typ.	Max.			
$V_{(BR)DSS}$	Drain-Source Breakdown voltage	$V_{GS} = 0\text{V}, I_D = 100\mu\text{A}$	800			V		
$V_{GS(th)}$	Gate Threshold voltage	$V_{GS} = V_{DS}, I_D = 2.2\text{mA}$		3.0		V	Fig. 9	
		$V_{GS} = V_{DS}, I_D = 2.2\text{mA}, T_j = 175^\circ\text{C}$		2.1				
I_{GSS}	Gate-Source Leakage current	$V_{GS} = 18\text{V}, V_{DS} = 0\text{V}$			250	nA		
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 800\text{V}, V_{GS} = 0\text{V}, T_j = 25^\circ\text{C}$		1	50	μA		
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS} = 15\text{V}, I_D = 5\text{A}$ $V_{GS} = 18\text{V}, I_D = 5\text{A}$		212	165	240	$\text{m}\Omega$	Fig. 3, 4, 5
		$V_{GS} = 15\text{V}, I_D = 5\text{A}, T_j = 175^\circ\text{C}$ $V_{GS} = 18\text{V}, I_D = 5\text{A}, T_j = 175^\circ\text{C}$		227	205			
g_{fs}	Transconductance	$V_{DS} = 18\text{V}, I_D = 5\text{A}$		5		S	Fig. 6	
		$V_{DS} = 18\text{V}, I_D = 5\text{A}, T_j = 175^\circ\text{C}$		4				



Gate Charge Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
Q _{GS}	Gate to Source Charge	$V_{DS} = 400V$ $I_D = 5A$ $V_{GS} = -4V/18V$		3.7		nC	Fig. 10
Q _{GD}	Gate to Drain Charge			7			
Q _G	Total Gate Charge			17.6			

AC Characteristics

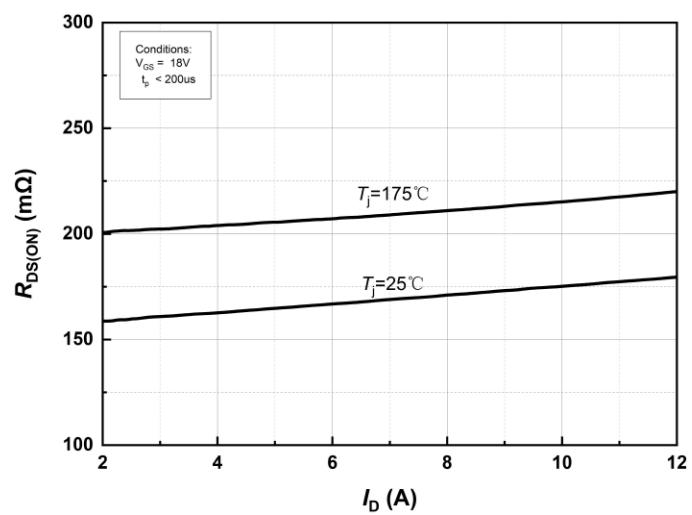
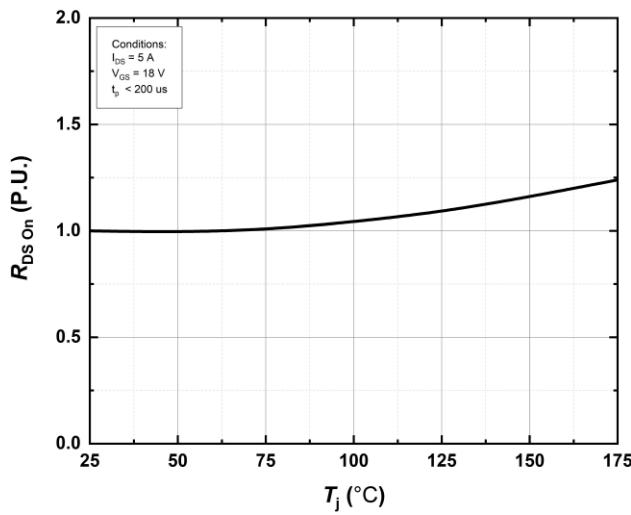
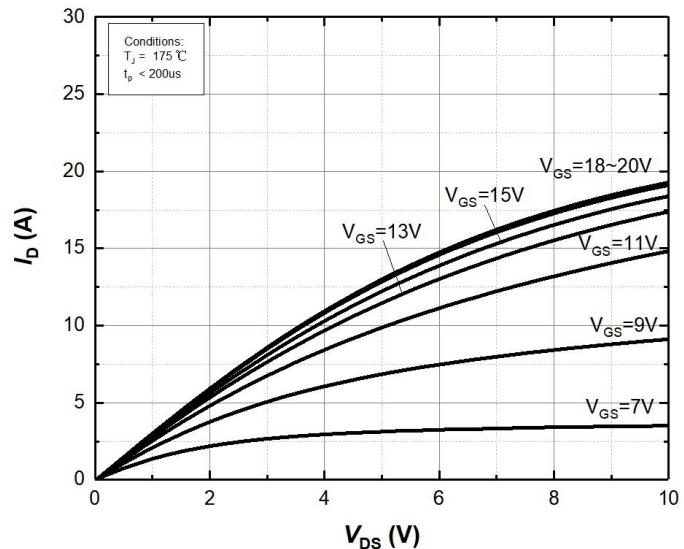
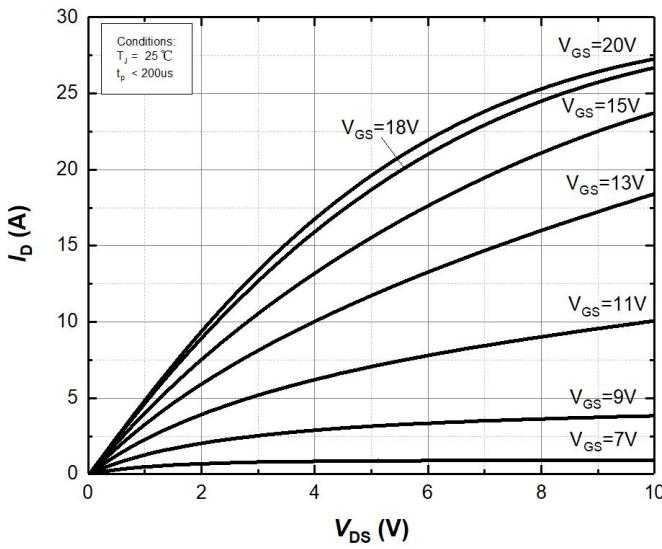
Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 600V$ $f = 1 \text{ MHz}$ $V_{AC} = 25mV$		361		pF	Fig. 13
C_{oss}	Output Capacitance			34		pF	
C_{rss}	Reverse Transfer Capacitance			3.5		pF	
$R_{G(int)}$	Internal Gate Resistance	$f = 1 \text{ MHz}, V_{AC} = 25mV$		3.5		Ω	

Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
V_{SD}	Diode Forward Voltage	$V_{GS} = -4V, I_{SD} = 2.5A$		3.8		V	Fig. 7,8
		$V_{GS} = -4V, I_{SD} = 2.5A, T_j = 175^\circ C$		3.4			
I_S	Continuous Diode Forward Current	$V_{GS} = -4V, T_C = 25^\circ C$		17		A	
$I_{S, pulse}$	Diode pulse Current	$V_{GS} = -4V$, pulse width t_p limited by T_{jmax}		26		A	



Typical Performance



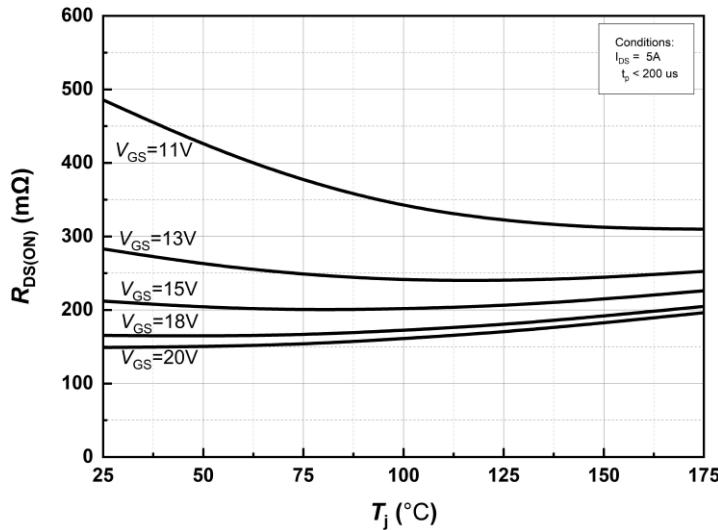


Figure 5. On-Resistance vs. Temperature for Various Gate Voltage

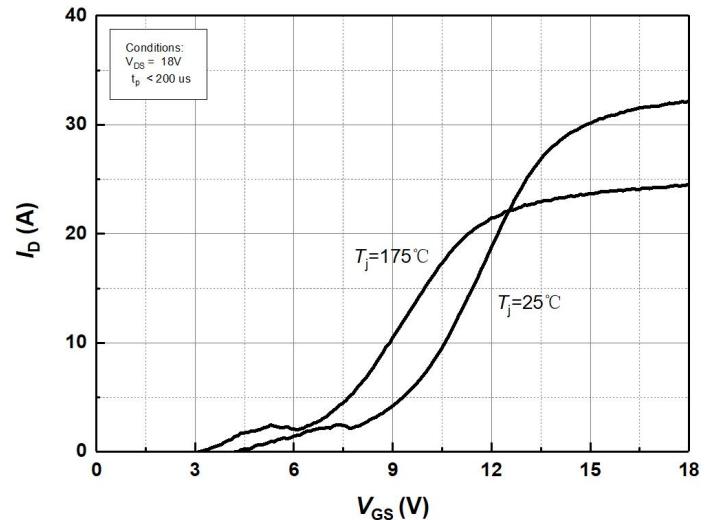


Figure 6. Transfer Characteristics for Various Junction Temperatures

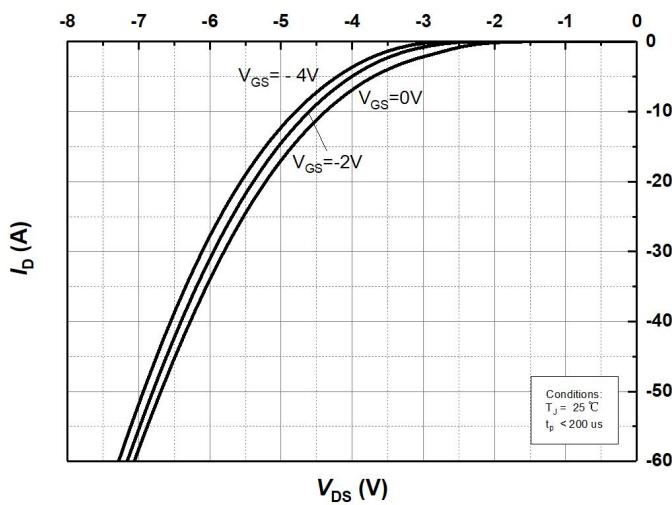


Figure 7. Body Diode Characteristics at $T_J=25^\circ\text{C}$

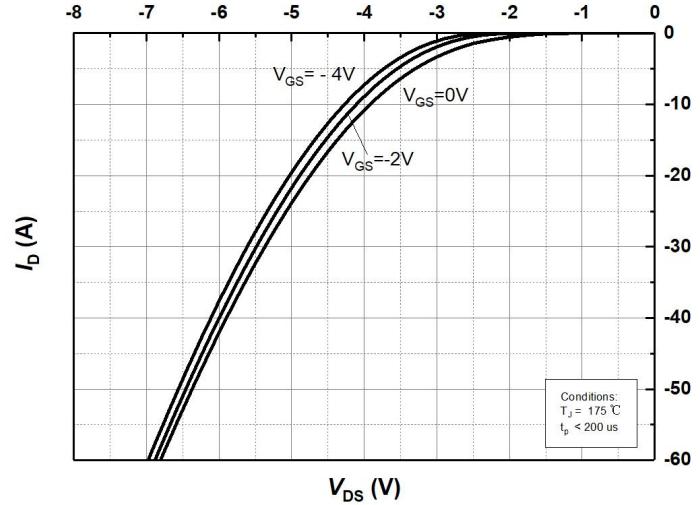


Figure 8. Body Diode Characteristics at $T_J=175^\circ\text{C}$

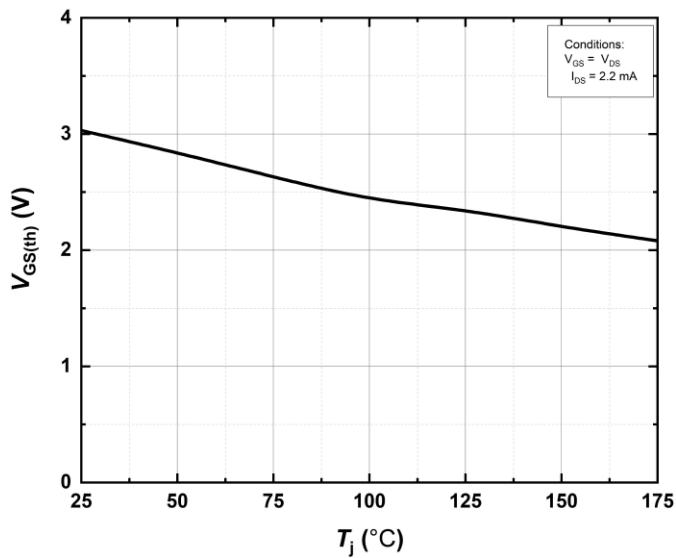


Figure 9. Threshold Voltage vs. Temperature

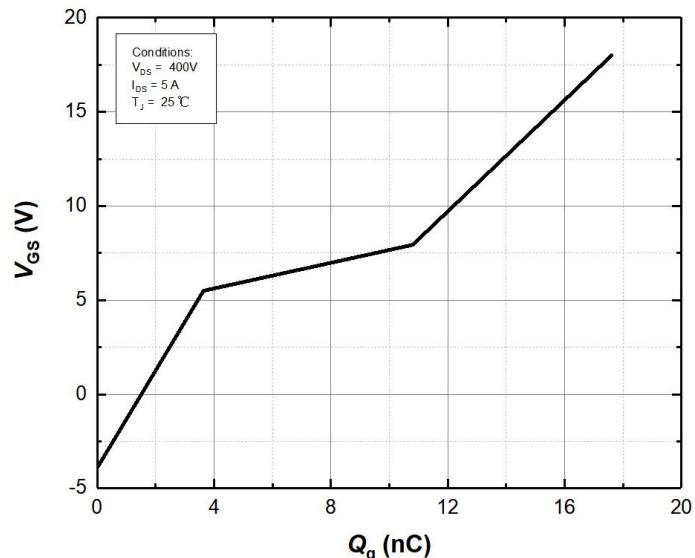


Figure 10 Gate Charge Characteristics

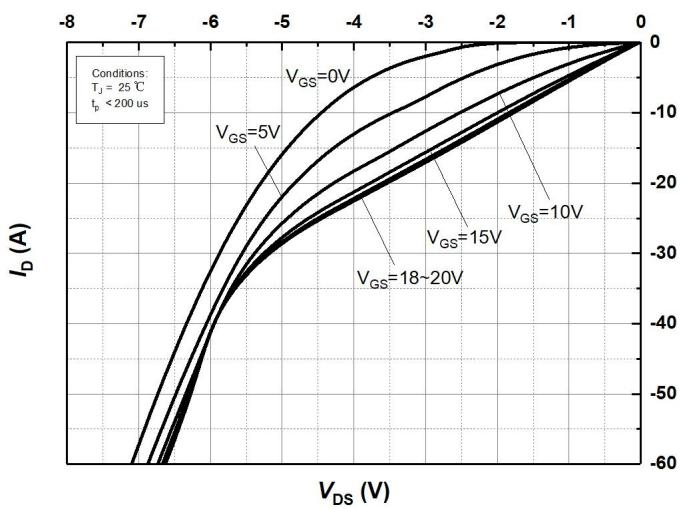


Figure 11. 3rd Quadrant Characteristic at $T_j=25^\circ C$

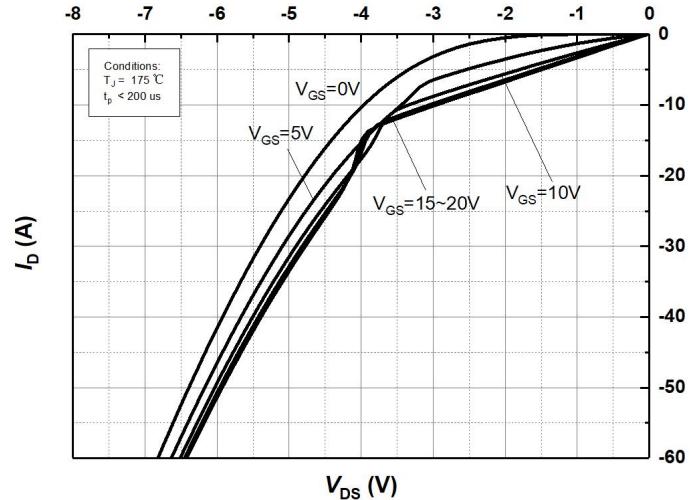


Figure 12. 3rd Quadrant Characteristic at $T_j=175^\circ C$

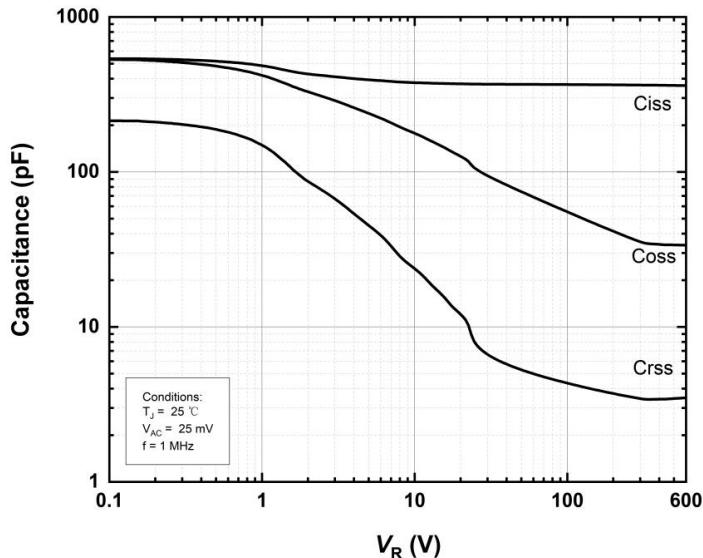


Figure 13. Capacitances vs. Drain-Source Voltage (0 – 600V)

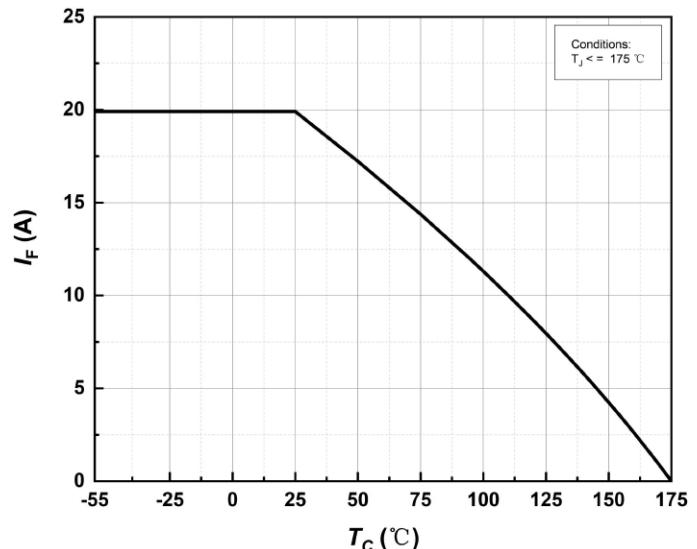


Figure 14. Continuous Drain Current Derating vs Case Temperature

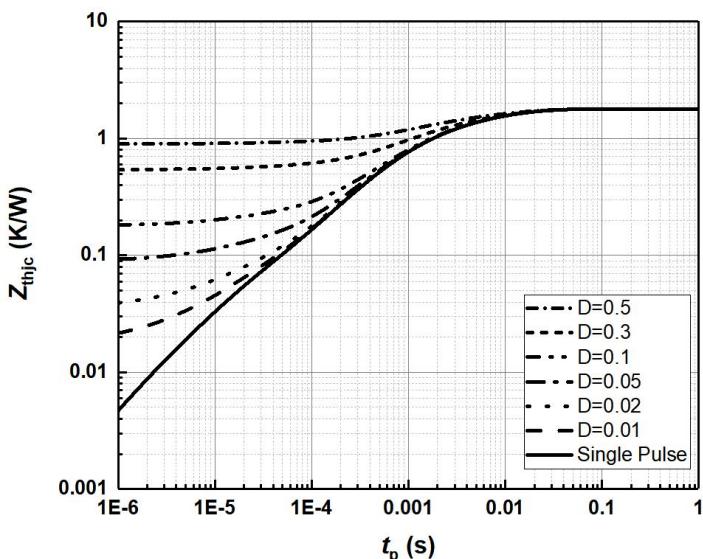


Figure 15. Transient Thermal Impedance (Junction – Case)

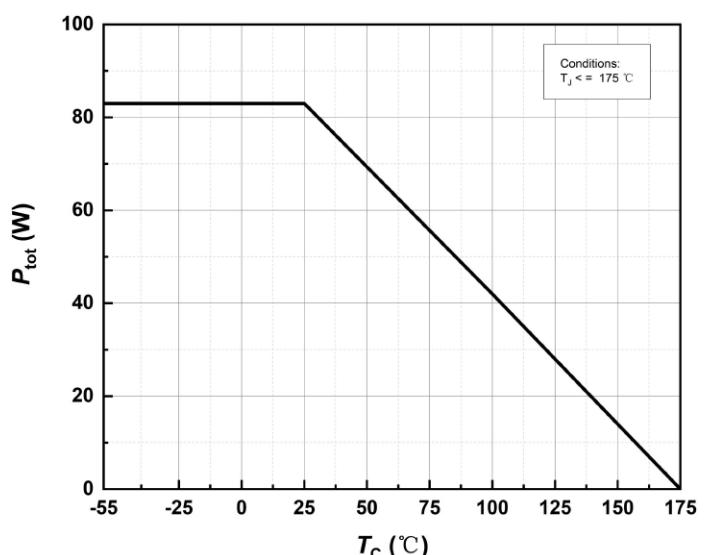


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

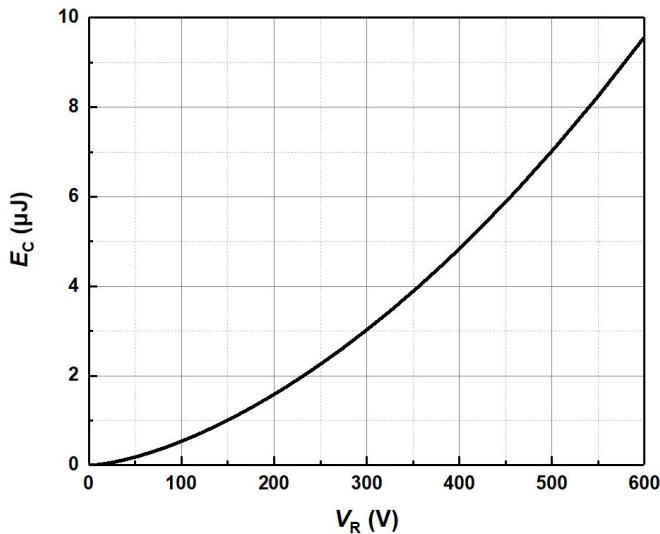


Figure 17. Output Capacitor Stored Energy

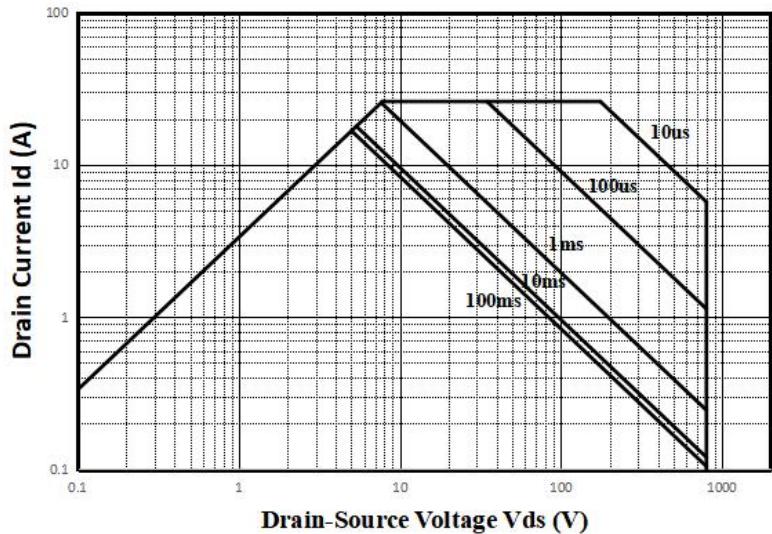
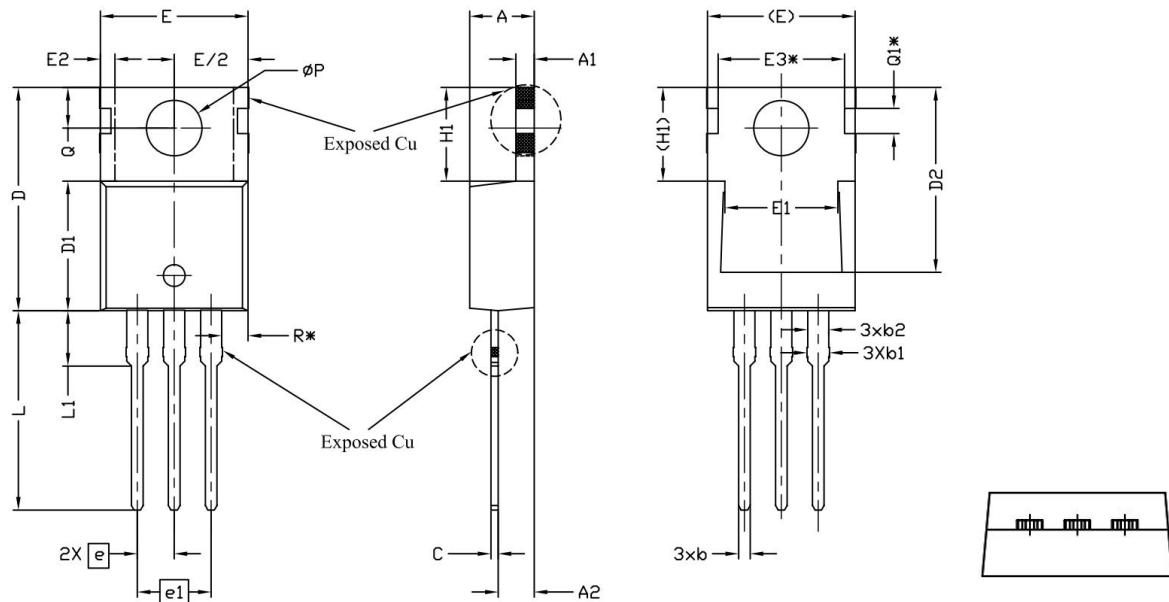


Figure 18. Safe Operating Area



Package Dimensions

Package TO-220C



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.24	4.44	4.64	
A1	1.15	1.27	1.40	
A2	2.30	2.48	2.70	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
c	0.40	0.50	0.60	
D	14.70	15.37	16.00	4
D1	8.82	8.92	9.02	
D2	12.43	12.73	12.83	5
E	9.96	10.16	10.36	4,5
E1	6.86	7.77	8.89	5
E2	-	-	0.76	6
E3*	8.70REF.			
e	2.54BSC			
e1	5.08BSC			
H1	6.30	6.45	6.60	5,6
L	13.47	13.72	13.97	
L1	3.60	3.80	4.00	
ØP	3.75	3.84	3.93	
Q	2.60	2.80	3.00	
Q1*	1.73REF.			
R*	1.82REF.			



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